



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

re the Application of: **KANO, Takashi**

Serial No.: **09/532,775**

Filed: **March 22, 2000**

#7/Amend a
Group Art Unit: 2828
9706
1/25/03

Examiner: **Tuan M. Nguyen**

P.T.O. Confirmation No.: 8757

For: **SEMICONDUCTOR LASER DEVICE**

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231
Sir:

January 18, 2003

In response to the Office Action dated **July 19, 2002**, extended to **January 19, 2003** by a 3 month Petition for Extension of Time, please amend the above-identified application as follows:

RECEIVED
TECHNOLOGY CENTER 2800
JAN 22 2003
U.S. PATENT AND TRADEMARK OFFICE

IN THE CLAIMS:

Please amend claims 1-3 as indicated below:

1. (Amended) A semiconductor laser device comprising:

a first nitride based semiconductor layer including a first conductivity type cladding layer and an active layer and containing at least one of boron, aluminum, gallium, indium and thallium;
a current blocking layer, formed on said first nitride based semiconductor layer, having a striped opening; and

A1